

SuperSpeed USB Passive Switch (Low/Full/Hi/SuperSpeed)

General Description

Features

The MAX14978 high-performance, passive analog switch is ideal for switching Hi-Speed USB and SuperSpeed USB data between one source and two loads, or vice versa. The device can be used in desktop and notebook applications where SuperSpeed USB ports are in limited supply. The device consists of two sets of analog switches with one set used for USB low-speed, full-speed, and Hi-Speed
Designed Low/Fi SuperSpeed USB
SuperSpeed USB ports are in limited supply. The device consists of two sets of analog switches with one set used for USB low-speed, full-speed, and Hi-Speed

signals and the second set used for USB SuperSpeed. The device operates from a single +3.3V supply.

The device features low insertion loss for all speeds. It has ± 6 kV Human Body Model (HBM) ESD protection on all I/O pins. In addition, the low/full/Hi-Speed COM_ ports have ESD protection to ± 15 kV HBM and ± 8 kV IEC 61000-4-2 contact.

The device is available in a small, 3.5mm x 9.0mm, 42-pin TQFN package and is specified over the extended -40°C to +85°C temperature range.

Applications

Desktop PCs Laptop PCs Industrial USB Switching

Designed for SuperSpeed USB Applications: Low/Full/Hi-Speed (1.5/12/480Mbps) SuperSpeed (5.0Gbps)

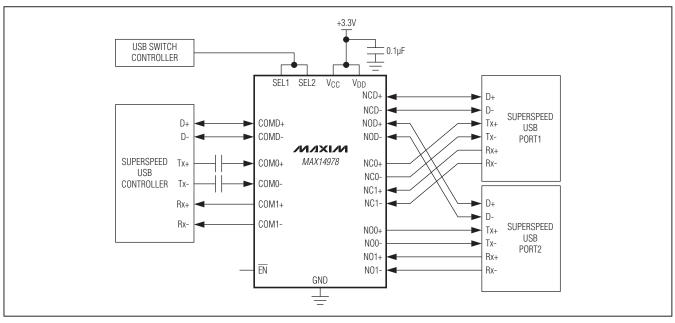
- Superior Return Loss and Insertion Loss for SuperSpeed Analog Switches
- Low Quiescent Current: 36µA (typ)
- All Link Training is Preserved (SuperSpeed)
- LVCMOS Control $(1.4V \le V_{IH} \le 3.6V)$
- Operation from a Single +3.3V Power Supply
- Small, 3.5mm x 9.0mm, 42-Pin TQFN Package

Ordering Information

| PART | TEMP RANGE | PIN-PACKAGE |
|--------------|----------------|-------------|
| MAX14978ETO+ | -40°C to +85°C | 42 TQFN-EP* |
| | <i></i> | |

+Denotes a lead(Pb)-free/RoHS-compliant package. *EP = Exposed pad.

Typical Operating Circuit



Maxim Integrated Products 1

MAX14978

For pricing, delivery, and ordering information, please contact Maxim Direct at 1-888-629-4642, or visit Maxim's website at www.maxim-ic.com.

ABSOLUTE MAXIMUM RATINGS

| (All voltages referenced to GND, unless otherwise noted.) V _{CC} 0.3V to +6.0V V _{DD} 0.3V to +4.0V | Peak Current (COM0_, COM1_ to NO0_, NO1_, NC0_, NC1_) (pulsed at 1ms, 10% duty cycle)±70mA Continuous Current into Any Terminal±30mA |
|---|--|
| SEL1, EN, COMD_, NOD_, | Continuous Power Dissipation ($T_A = +70^{\circ}C$) |
| NCD_ (Note 1)0.3V to (V _{CC} + 0.3V) | TQFN (derate 35.7mW/°C above +70°C) |
| SEL2, COM0_, COM1_, NC0_, | Operating Temperature Range40°C to +85°C |
| NC1_, NO0_, NO1_ (Note 1)0.3V to (V _{DD} + 0.3V) | Storage Temperature Range65°C to +150°C |
| ICOM0 NO0_I, ICOM0 NC0_I, | Junction Temperature+150°C |
| ICOM0 NO1 _I, ICOM0 NC1_I (Note 1) 0 to +2.0V | Lead Temperature (soldering, 10s)+300°C |
| Continuous Current (COM0_, | Soldering Temperature (reflow)+260°C |
| COM1_ to NO0_, NO1_, NC0_, NC1_) ±70mA | |

Note 1: Signals on SEL_, NO_, NC_, or COM_ exceeding VCC, VDD, or VGND are clamped by internal diodes. Limit forward-diode current to maximum current rating.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ELECTRICAL CHARACTERISTICS

 $(V_{CC} = +3.0V \text{ to } +5.5V, V_{DD} = +3.0V \text{ to } +3.6V, T_{A} = -40^{\circ}\text{C} \text{ to } +85^{\circ}\text{C}, \text{ unless otherwise noted. Typical values are at } V_{CC} = V_{DD} = +3.3V, T_{A} = +25^{\circ}\text{C}.)$ (Note 2)

| PARAMETER | SYMBOL | CONDITIONS | | MIN | ТҮР | MAX | UNITS |
|--|----------------------------|---|-----------------|-----------------------|-----------------------|--------------------------|-------|
| Dower Supply Dopes | Vcc | | | 3.0 | | 5.5 | V |
| Power-Supply Range | VDD | | | 3.0 | | 3.6 | V |
| Supply Current | Icc | $V_{SEL1} = 0V \text{ or } V_{CC}, V_{\overline{EN}} = 0V$ | VCC = 3.0V | | 0.6 | 1.5 | |
| Supply Current | IDD | V _{SEL2} = 0V or V _{DD} | $V_{DD} = 3.3V$ | | | 60 | μΑ |
| Shutdown Supply Current, ICC | ISHDN | Hi-Speed USB switches, switc (VEN = VCC) | h disabled | | 0.1 | | μA |
| Increase in Supply Current, ICC, with V_{SEL1} , $V_{\overline{EN}}$ Voltage | | $ \begin{array}{l} \mbox{Hi-Speed USB switches, 0V \leq } \\ \mbox{or } V_{IH} \leq V_{SEL1} \leq V_{CC} \mbox{ or } 0V \leq V \\ \mbox{VIH} \leq V_{\overline{EN}} \leq V_{CC} \end{array} $ | | | | 1 | μA |
| Angles Cisnel Dense | VCOM_, | Hi-Speed USB switches, $V_{\overline{EN}} = 0V$ (Note 3) | | 0 | | Vcc | V |
| Analog Signal Range | V _{NO_} , VNC_ | SuperSpeed USB switches | | -0.3 | | V _{DD} - 1.2 | V |
| Fault-Protection Trip Threshold | VFP | Hi-Speed USB switches, COMD_ only, TA = +25°C | | V _{CC} + 0.6 | V _{CC} + 0.8 | V _{CC} + 1 | V |
| | | Hi-Speed USB switches, VCOMD_ = 0V to VCC | | | 5 | 10 | |
| On-Resistance | RON | Hi-Speed USB switches, V _{CC} = V _{COMD} = 3.6V | = 3.0V, | | 5.5 | | Ω |
| | | SuperSpeed USB switches, V _E ICOM_ = 15mA, V _{NO} _ = V _{NC} _ | | | 7 | | |

ELECTRICAL CHARACTERISTICS (continued)

 $(V_{CC} = +3.0V \text{ to } +5.5V, V_{DD} = +3.0V \text{ to } +3.6V, T_A = -40^{\circ}\text{C} \text{ to } +85^{\circ}\text{C}, \text{ unless otherwise noted. Typical values are at } V_{CC} = V_{DD} = +3.3V, T_A = +25^{\circ}\text{C}.)$ (Note 2)

| PARAMETER | SYMBOL | CONDITION | IS | MIN | ТҮР | MAX | UNITS |
|---|-------------------|---|-------------------------|------|------|------|-------|
| On Desistance Match Detugen | | Hi-Speed USB switches, V VCOMD_ = 2.0V (Notes 4, 5 | | 0.1 | 1 | | |
| On-Resistance Match Between Channels | ΔR _{ON} | SuperSpeed USB switches I _{COM} = 15mA, V _{NO} or V ₁ (Notes 4, 5) | | | 0.6 | 2 | Ω |
| On-Resistance Match Between Pairs of Same Channels | ΔRon | SuperSpeed USB switches, V _{DD} = 3.0V, ICOM_ = 15mA, V _{NO} _ or V _{NC} _ = 0V (Notes 4, 5) | | | 0.1 | 1 | Ω |
| | | Hi-Speed USB switches, V VCOMD_ = 0V to VCC (Note | | | 0.1 | | |
| On-Resistance Flatness | R _{FLAT} | SuperSpeed USB switches, $V_{DD} = 3.0V$, I _{COM} = 15mA, V_{NO} or $V_{NC} = 0V$ (Notes 5, 6) | | | 0.06 | 2 | Ω |
| 0111 | | Hi-Speed USB switches, V _{CC} = 5.5V, V _{COMD} = 0V or 5.5V, V _{NOD} , V _{NCD} = 5.5V or 0V | | -250 | | +250 | nA |
| Off-Leakage Current | ICOM(OFF) | SuperSpeed USB switches, $V_{DD} = 3.6V$, $V_{COM} = 0V$, 1.8V; V_{NO} or $V_{NC} = 1.8V$, 0V | | -1 | | +1 | μA |
| | | Hi-Speed USB switches, V _{CC} = 5.5V, V _{COMD} = 0V or 5.5V, V _{NOD} , V _{NCD} = unconnected SuperSpeed USB switches, V _{DD} = 3.6V, V _{COM} = 0V, 1.8V; V _{NO} or V _{NC} = V _{COM} or unconnected | | -250 | | +250 | nA |
| On-Leakage Current | ICOM(ON) | | | -1 | | +1 | μA |
| AC PERFORMANCE | | | | | | | |
| On-Channel -3dB Bandwidth | BW | Hi-Speed USB switches, R signal = 0dBm | $L = RS = 50\Omega$, | | 950 | | MHz |
| | | SuperSpeed USB | 1MHz < f < 100MHz | | -0.5 | | ٩D |
| On-Loss | GLOSS | switches, $R_L = R_S = 50\Omega$, unbalanced | 500MHz < f < 1.25GHz | | -1.4 | | - dB |
| | | Hi-Speed USB switches, | f = 10MHz | | -48 | | |
| | | VNOD_, VNCD_ = 0dBm, | f = 250MHz | | -20 | | - dB |
| Off-Isolation | VISO | VISO $R_L = R_S = 50\Omega$, Figure 1 | f = 500MHz | | -17 | | |
| | | SuperSpeed USB switches, signal = 0dBm, | f = 10MHz | | -56 | | |
| | | $\begin{vmatrix} \text{switches, signal = 00Bin,} \\ \text{R}_{\text{S}} = \text{R}_{\text{L}} = 50\Omega \qquad \qquad$ | | | -26 | | |

ELECTRICAL CHARACTERISTICS (continued)

 $(V_{CC} = +3.0V \text{ to } +5.5V, V_{DD} = +3.0V \text{ to } +3.6V, T_{A} = -40^{\circ}\text{C} \text{ to } +85^{\circ}\text{C}, \text{ unless otherwise noted. Typical values are at } V_{CC} = V_{DD} = +3.3V, T_{A} = +25^{\circ}\text{C}.)$ (Note 2)

| PARAMETER | SYMBOL | CONDITIONS | | MIN | ТҮР | MAX | UNITS |
|--------------------------------|------------|---|---|------|-----|------|-------|
| | | Hi-Speed USB switches, | f = 10MHz | | -73 | | |
| | | $V_{NOD_{-}}, V_{NCD_{-}} = 0 dBm,$ | f = 250MHz | | -54 | | |
| | | $R_L = R_S = 50\Omega$, Figure 1 | f = 500MHz | | -33 | | |
| Crosstalk (Note 7) | VCT | SuperSpeed USB switch- es, crosstalk between any two pairs, | f = 50MHz | | -53 | | dB |
| | | $R_S = R_L = 50\Omega$, unbal- anced, Figure 1 | f = 1.25GHz | | -32 | | |
| Signaling Data Rate | BR | SuperSpeed USB switches, $R_S = R_L = 50\Omega$ | | | 5.0 | | Gbps |
| LOGIC INPUT | | | | | | | |
| Input Logic-High | VIH | | | 1.4 | | | V |
| Input Logic-Low | VIL | | | | | 0.5 | V |
| | | Hi-Speed USB switches | | -250 | | +250 | nA |
| Input Leakage Current | liN | SuperSpeed USB switches VSEL2 = 0V or VDD | , | -1 | | +1 | μA |
| Input Logic Hysteresis | Vhyst | SuperSpeed USB switches | | | 100 | | mV |
| DYNAMIC PERFORMANCE | - | • • • | | | | | |
| Turn-On Time | ton | Hi-Speed USB switches, V _{NOD} or V _{NCD} = 1.5V, R C _L = 35pF, V <u>EN</u> = V _{CC} to C | | | 20 | 100 | μs |
| | | SuperSpeed USB switches, $V_{NO_{-}}$ or $V_{NC_{-}}$ = 1.0V, R_{L} = 50 Ω , Figure 2 | | | 90 | 250 | ns |
| T 0// T | | V_{NOD} or V_{NCD} = 1.5V, R C _L = 35pF, $V_{\overline{EN}}$ = 0V to VC | | | 1 | 5 | μs |
| Turn-Off Time | tOFF | | SuperSpeed USB switches, V_{NO} or V_{NC} = 1.0V, R_L = 50 Ω , Figure 2 | | 10 | 50 | ns |
| Propagation Delay | tplh, tphl | Hi-Speed USB switches, R Figure 3 | $L = R_S = 50\Omega$, | | 100 | | ps |
| | | SuperSpeed USB switches, $R_L = R_S = 50\Omega$ | | | 50 | | |
| Output Skew Between Switches | tsĸ | Hi-Speed USB switches, skew between switch 1 and 2, $R_L = R_S = 50\Omega$, Figure 3 | | | 40 | | ps |
| Output Skew Between Pairs | tSK1 | SuperSpeed USB switches, $R_S = R_L = 50\Omega$, unbalanced; skew between any two pairs, Figure 3 | | | 50 | | ps |
| Output Skew Between Same Pair | tSK2 | SuperSpeed USB switches, $R_S = R_L = 50\Omega$, unbalanced; skew between two lines on same pair, Figure 3 | | | 10 | | ps |
| Fault-Protection Response Time | tFP | Hi-Speed USB switches, V _{COMD} = 0V to 5V step, R V _{CC} = 3.3V, Figure 4 | $L = R_S = 50\Omega,$ | 0.5 | | 5.0 | μs |

ELECTRICAL CHARACTERISTICS (continued)

 $(V_{CC} = +3.0V \text{ to } +5.5V, V_{DD} = +3.0V \text{ to } +3.6V, T_A = -40^{\circ}\text{C} \text{ to } +85^{\circ}\text{C}, \text{ unless otherwise noted}. Typical values are at V_{CC} = V_{DD} = +3.3V, T_A = +25^{\circ}\text{C}.)$ (Note 2)

| PARAMETER | SYMBOL | CONDITIONS | MIN | TYP | MAX | UNITS | |
|---|----------------------------|--|-----|------|-----|-------|--|
| Fault-Protection Recovery Time | tepr | Hi-Speed USB switches, V _{COMD} = 5V to 0V step, R _L = R _S = 50 Ω , V _{CC} = 3.3V, Figure 4 | | | 100 | μs | |
| NO_ or NC_ Off-Capacitance | C _{NO(OFF)} or | Hi-Speed USB switches, f = 1MHz, Figure 5 | | 2 | | pF | |
| | CNC(OFF) | SuperSpeed USB switches, Figure 5 | | 1 | | | |
| 00M 0# 0 | 0 | Hi-Speed USB switches, f = 1MHz, Figure 5 | | 5.5 | | | |
| COM_ Off-Capacitance | CCOM(OFF) | Hi-Speed USB switches, f = 240MHz, Figure 5 | | 4.8 | | - pF | |
| | | Hi-Speed USB switches, f = 1MHz, Figure 5 | | 6.5 | | | |
| COM_ On-Capacitance | CCOM(ON) | Hi-Speed USB switches, f = 240MHz, Figure 5 | | 5.5 | | pF | |
| | | SuperSpeed USB switches, Figure 5 | | 2 | | | |
| Total Harmonic Distortion Plus Noise | THD+N | Hi-Speed USB switches, VCOMD_ = 1VP-P, VBIAS = 1V, RL = RS = 50 Ω , f = 20Hz to 20kHz | | 0.03 | | % | |
| ESD PROTECTION | | | | | | | |
| | | Human Body Model | | ±15 | | | |
| COMD+, COMD- | | IEC 61000-4-2 Air Gap Discharge | | ±15 | | kV | |
| | | IEC 61000-4-2 Contact Discharge | | ±8 | | | |
| COM0_, COM1_ | | Human Body Model | | ±6 | | kV | |
| All Pins | | Human Body Model | | ±2 | | kV | |

Note 2: All devices are 100% production tested at $T_A = +25^{\circ}C$. All temperature limits are guaranteed by design.

Note 3: The switch turns off for voltages above VFP, protecting downstream circuits in case of a fault condition.

Note 4: $\Delta R_{ON(MAX)} = |R_{ON(CH1)} - R_{ON(CH2)}|$.

Note 5: Guaranteed by design. Not production tested.

Note 6: Flatness is defined as the difference between the maximum and minimum value of on-resistance, as measured over specified analog-signal ranges.

Note 7: Between any two switches.

Test Circuits/Timing Diagrams

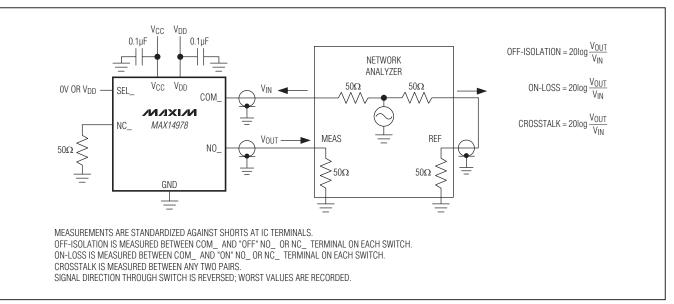


Figure 1. Off-Isolation, On-Loss, and Crosstalk

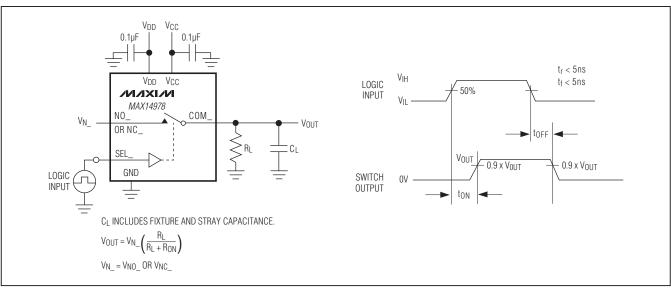


Figure 2. Switching Time

Test Circuits/Timing Diagrams (continued)

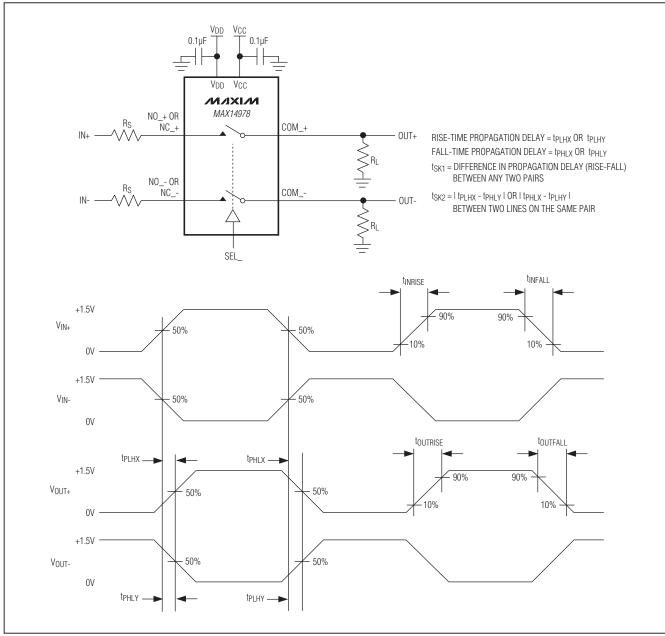


Figure 3. Propagation Delay, Output Skew

MAX14978

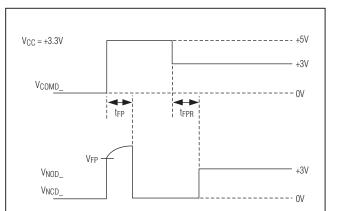
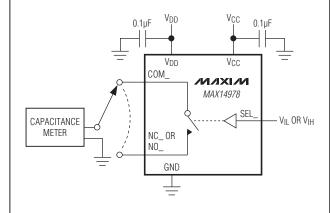


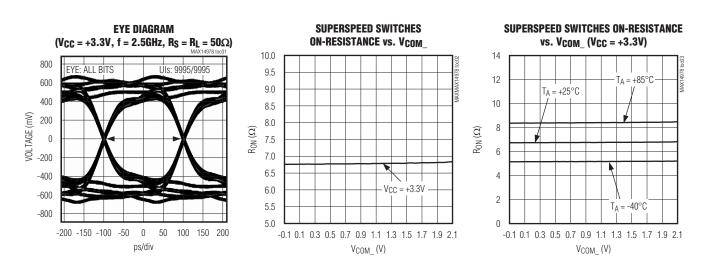
Figure 4. Fault Protection Response/Recovery Time

Test Circuits/Timing Diagrams (continued)



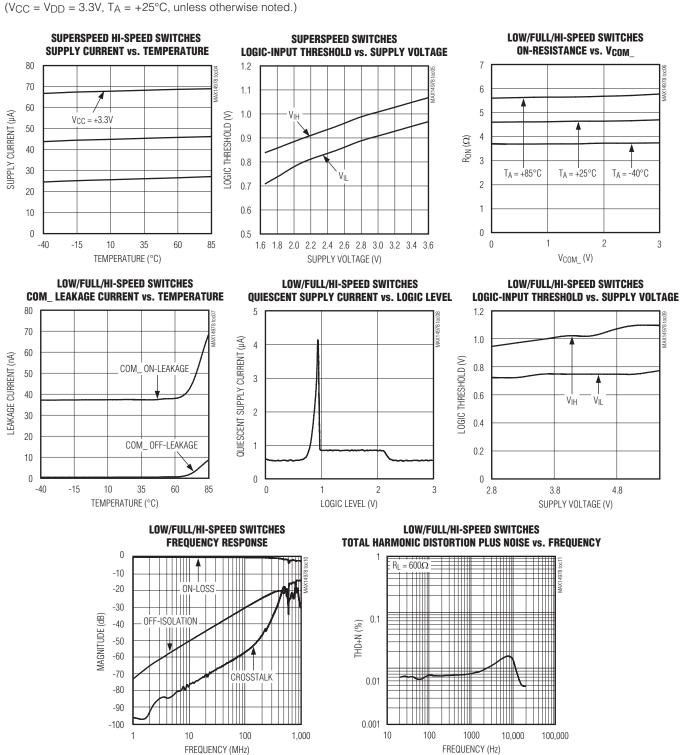


(V_{CC} = V_{DD} = 3.3V, T_A = $+25^{\circ}C$, unless otherwise noted.)



Typical Operating Characteristics

Typical Operating Characteristics (continued)



MAX14978

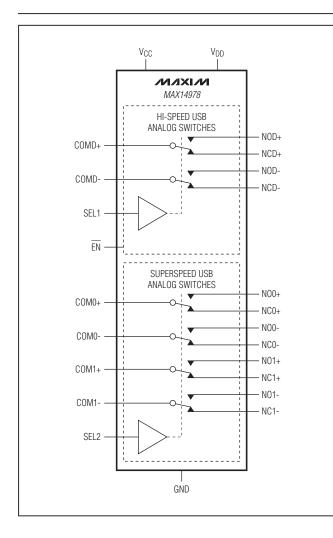
Pin Configuration TOP VIEW 38 37 36 35 34 33 32 31 30 29 28 27 26 25 24 23 22 21 GND N.C. 39 /VI/XI/VI N.C. 40 20 V_{DD} MAX14978 N.C. 41 19 GND N.C. 42 EP 18 VDD 1 2 3 4 5 6 7 8 9 10 11 12 13 14 15 16 17 N.C. N.C. N.C. N.C. COMD+ N.C. SEL2 SEL2 GND-COM0+ COM0+ COM0+ COM0+ COM1+ COM1-COM1+ COM1-COM1-COM1-COM1-COM1-COM1-COM1-COM2-CO TQFN

Pin Description

| PIN | NAME | FUNCTION |
|--------------------------------|-------|--|
| 1, 2, 3, 6, 8, 36, 39–42 | N.C. | No Connection. Not internally connected. |
| 4 | COMD+ | Hi-Speed USB Analog Switch, Common D+ Terminal |
| 5, 10, 14, 17, 19, 21 | GND | Ground |
| 7 | COMD- | Hi-Speed USB Analog Switch, Common D- Terminal |
| 9 | SEL2 | Digital Control Input for SuperSpeed USB Analog Switches |
| 11 | COM0+ | SuperSpeed USB Analog Switch 0, Common Positive Terminal |
| 12 | COM0- | SuperSpeed USB Analog Switch 0, Common Negative Terminal |
| 13, 18, 20, 30 | VDD | Positive Supply Voltage Input for SuperSpeed USB Switches. Bypass V_{DD} to GND with a 0.1µF ceramic capacitor as close as possible to the device. |
| 15 | COM1+ | SuperSpeed USB Analog Switch 1, Common Positive Terminal |
| 16 | COM1- | SuperSpeed USB Analog Switch 1, Common Negative Terminal |
| 22 | NO1- | SuperSpeed USB Analog Switch 1, Normally Open Negative Terminal |
| 23 | NO1+ | SuperSpeed USB Analog Switch 1, Normally Open Positive Terminal |
| 24 | NO0- | SuperSpeed USB Analog Switch 0, Normally Open Negative Terminal |
| 25 | NO0+ | SuperSpeed USB Analog Switch 0, Normally Open Positive Terminal |
| 26 | NC1- | SuperSpeed USB Analog Switch 1, Normally Closed Negative Terminal |
| 27 | NC1+ | SuperSpeed USB Analog Switch 1, Normally Closed Positive Terminal |
| 28 | NC0- | SuperSpeed USB Analog Switch 0, Normally Closed Negative Terminal |
| 29 | NC0+ | SuperSpeed USB Analog Switch 0, Normally Closed Positive Terminal |
| 31 | NOD- | Hi-Speed USB Analog Switch, Normally Open D- Terminal |
| 32 | NCD- | Hi-Speed USB Analog Switch, Normally Closed D- Terminal |

Pin Description (continued)

| PIN | NAME | FUNCTION |
|-----|------|---|
| 33 | ĒN | Active-Low Enable Input for Hi-Speed USB Switches. Drive \overline{EN} high to put Hi-Speed USB switches in high impedance. Drive \overline{EN} low for normal operation. |
| 34 | Vcc | Positive-Supply Voltage Input for Hi-Speed USB Switches. Bypass V_{CC} to GND with a 0.1µF ceramic capacitor as close as possible to the device. |
| 35 | SEL1 | Digital Control Input for Hi-Speed USB Analog Switches |
| 37 | NCD+ | Hi-Speed USB Analog Switch, Normally Closed D+ Terminal |
| 38 | NOD+ | Hi-Speed USB Analog Switch, Normally Open D+ Terminal |
| _ | EP | Exposed Pad. EP is internally connected to GND. Connect EP to a large ground plane to maximize thermal performance. EP is not intended as an electrical connection point. |



Functional Diagram/Truth Table

| HI-SPEED USB SWITCHES | | | | | | | |
|-----------------------|---|-----|-----|--------|--|--|--|
| EN SEL1 NOD NCD COMD | | | | | | | |
| 0 | 0 | OFF | ON | _ | | | |
| 0 | 1 | ON | OFF | _ | | | |
| 1 | Х | OFF | OFF | HIGH-Z | | | |

| SUPERSPEED USB SWITCHES | | | | | |
|-------------------------|-----|-----|--|--|--|
| SEL2 NO_ NC_ | | | | | |
| 0 | OFF | ON | | | |
| 1 | ON | OFF | | | |

MAX14978

Detailed Description

The MAX14978 is ideal for SuperSpeed USB and low/ full/Hi-Speed (1.5/12/480Mbps) USB switching applications. The low V_{IH} threshold of the device permits it to be used with logic levels as low as 1.4V. The device's Hi-Speed USB analog switches are based on a chargepump-assisted n-channel architecture and operate with 36µA (typ) quiescent current. The device features dual digital control inputs (SEL_) to switch Hi-Speed USB and SuperSpeed USB signal paths separately.

Digital Control Inputs (SEL1, SEL2)

The device's provides dual digital control inputs (SEL1, SEL2) to select the signal path between the COM_ and NO_ or NC_ channels. Drive SEL1 and SEL2 rail-to-rail to minimize power consumption. See the *Functional Diagram/Truth Table*.

Analog-Signal Levels

The device's switches are bidirectional, allowing NO_, NC_, and COM_ to be configured as either inputs or outputs.

The Hi-Speed USB switches are equipped with a chargepump-assisted n-channel architecture that allows the switch to pass analog signals that exceed V_{CC} up to the overvoltage fault-protection threshold. This allows USB signals that exceed V_{CC} to pass, allowing compliance with USB requirements for voltage levels.

The SuperSpeed USB switches accept signals on the COM_, NO_, and NC_ channels within a range of -0.1V to (V_{DD} - 1.2V). Signals on the COM_+ channels are routed to either the NO_+ or NC_+ channels, and signals on the COM_- channels are routed to either the NO_- or NC_- channels.

Overvoltage Fault Protection

The device features overvoltage fault protection on COMD_. Fault protection prevents these switches from being damaged due to shorts to the USB VBUS voltage rail. Fault protection protects the switch and USB transceiver from damaging voltage levels. When voltages on COMD_ exceed the fault-protection threshold (VFP), COMD_, NCD_ and NOD_ are high impedance.

Enable Input

The device features a shutdown mode for the Hi-Speed USB analog switches that reduces the V_{CC} quiescent current to 0.1 μ A (typ) and places COMD+ and COMD-in high impedance. Drive EN high to place the Hi-Speed USB analog switches in shutdown mode, and drive EN low for normal operation.

Applications Information

USB Switching

The device's analog switches are fully compliant with the USB 2.0 and USB 3.0 specifications. The low on-resistance and low on-capacitance of these switches make them ideal for high-performance switching applications. The device is ideal for routing USB data lines and for applications that require switching between multiple USB hosts or devices. The device's Hi-Speed USB analog switches also feature overvoltage fault protection to guard systems against shorts to the USB vBUS voltage rail that is required for all Hi-Speed USB applications.

Extended ESD Protection

As with all Maxim devices, ESD protection structures are incorporated on all pins to protect against electrostatic discharges encountered during handling and assembly. COMD+ and COMD- are further protected against static electricity. Maxim's engineers have developed state-ofthe-art structures to protect these pins against ESD up to ± 15 kV without damage. The ESD structures withstand high ESD in normal operation and when the device is powered down. After an ESD event, the device continues to function without latchup.

The device is characterized for protection to the following limits:

- ±15kV using Human Body Model
- ±15kV using IEC 61000-4-2 Air Gap Discharge method
- ±8kV using IEC 61000-4-2 Contact Discharge method

Note: High ESD performance is only applicable to the Hi-Speed USB section of the switch. The SuperSpeed USB section is rated to ± 6 kV HBM.

ESD Test Conditions

ESD performance depends on a variety of conditions. Contact Maxim for a reliability report that documents test setup, test methodology, and test results.

Human Body Model

Figure 6a shows the Human Body Model, and Figure 6b shows the current waveform it generates when discharged into a low-impedance state. This model consists of a 100pF capacitor charged to the ESD voltage of interest, which is then discharged into the test device through a $1.5 \mathrm{k}\Omega$ resistor.

IEC 61000-4-2

The main difference between tests done using the Human Body Model and IEC 61000-4-2 is higher peak current in IEC 61000-4-2. Because series resistance is lower in the IEC 61000-4-2 ESD test model (Figure 7a) the ESDwithstand voltage measured to this standard is generally

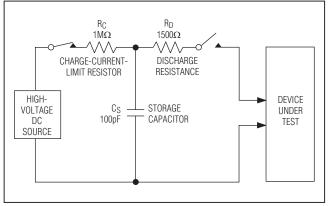


Figure 6a. Human Body ESD Test Model

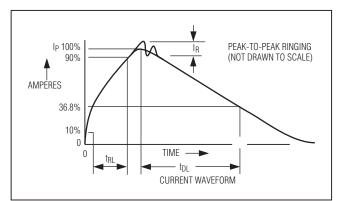


Figure 6b. Human Body Current Waveform

lower than that measured using the Human Body Model. Figure 7b shows the current waveform for the $\pm 8kV$ IEC 61000-4-2 Level 4 ESD Contact Discharge test.

The Air Gap Discharge test involves approaching the device with a charged probe. The Contact Discharge method connects the probe to the device before the probe is energized.

Layout

High-speed switches require proper layout and design procedures for optimum performance. Keep designcontrolled impedance PCB traces as short as possible or follow impedance layouts per the SuperSpeed USB specification. Ensure that power-supply bypass capacitors are placed as close as possible to the device. Multiple bypass capacitors are recommended. Connect all grounds and the exposed pad to large ground planes where possible.

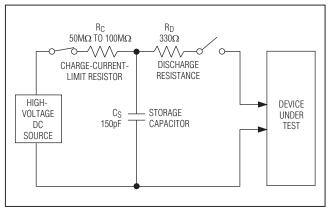


Figure 7a. IEC 61000-4-2 ESD Test Model

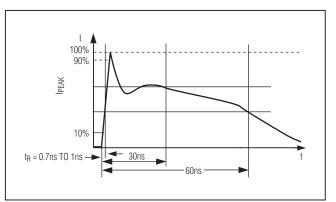


Figure 7b. IEC 61000-4-2 ESD Generator Current Waveform

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Power-Supply Sequencing

Caution: Do not exceed the absolute maximum ratings because stresses beyond the listed ratings may cause permanent damage to the device.

Proper power-supply sequencing is recommended for all CMOS devices. Always apply VCC and VDD before applying analog signals, especially if the analog signals are not current limited.

_Package Information

For the latest package outline information and land patterns (footprints), go to <u>www.maxim-ic.com/packages</u>. Note that a "+", "#", or "-" in the package code indicates RoHS status only. Package drawings may show a different suffix character, but the drawing pertains to the package regardless of RoHS status.

| PACKAGE | PACKAGE | OUTLINE | LAND |
|------------|------------|----------------|----------------|
| TYPE | CODE | NO. | PATTERN NO. |
| 42 TQFN-EP | T423590M+1 | <u>21-0181</u> | <u>90-0079</u> |

Revision History

| REVISION NUMBER | REVISION DATE | DESCRIPTION | PAGES CHANGED |
|--------------------|------------------|--|------------------|
| 0 | 9/10 | Initial release | — |
| 1 | 4/11 | Updated analog signal range specification in <i>Electrical Characteristics</i> | 2 |

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